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8/9/01

Docket No: 0756-2330

IN THE U.S. PATENT AND TRADEMARK OFFICE

IN RE PATENT APPLICATION OF:) Art Unit: 2823
Shunpei YAMAZAKI et al) Ex.: B. Kebede
SERIAL NO. 09/894,125)
FILED: 06/29/2001)
FOR: CRYSTALLINE SEMICONDUCTOR)
THIN FILM, METHOD OF)
FABRICATING THE SAME,)
SEMICONDUCTOR DEVICE AND)
METHOD OF FABRICATING THE SAME)

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PRELIMINARY AMENDMENT

Honorable Commissioner for Patents
U.S. Patent and Trademark Office
Washington, D.C. 20231
Sir:

Please preliminarily amend the above identified patent application as follows:

In the Claims:

Please add the following new claims 19-26:

A1

19. (New) A method of manufacturing a semiconductor device comprising the steps of:

C3

forming a semiconductor film comprising silicon over a substrate;
irradiating said semiconductor film with laser light in an atmosphere containing oxygen for crystallizing said semiconductor film;
removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and